

October 2008

# **KSC5021 NPN Silicon Transistor**

- High Voltage and High Reliability
- High Speed Switching :  $t_F = 0.1 \mu s$  (Typ.)
- · Wide SOA



1.Base 2.Collector 3.Emitter

### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	5	А
I <sub>CP</sub>	Collector Current (Pulse)	10	А
I <sub>B</sub>	Base Current	2	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	50	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA, I <sub>E</sub> = 0	800			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0	500			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA, I <sub>C</sub> = 0	7			V
V <sub>CEX</sub> (sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 2.5A, I <sub>B1</sub> = -I <sub>B2</sub> = 1A L = 1mH, Clamped	500			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 500V, I <sub>E</sub> = 0			10	μА
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0			10	μА
h <sub>FE1</sub>	DC Current Gain	V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.6A V <sub>CE</sub> = 5V, I <sub>C</sub> = 3A	15 8		50	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A, I <sub>B</sub> = 0.6A			1	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A, I <sub>B</sub> = 0.6A			1.5	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f=1MHz		80		pF
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = 10V, I <sub>C</sub> = 0.6A		18		MHz
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = 200V			0.5	μS
t <sub>STG</sub>	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 4A$ $R_1 = 50\Omega$			3	μS
t <sub>F</sub>	Fall Time				0.3	μS

<sup>\*</sup> Pulse Test: PW  $\leq 300 \mu s, \, \text{Duty Cycle} \leq 2\%$ 

# h<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE1</sub>	15 ~ 30	20 ~ 40	30 ~ 50

### **Typical Performance Characteristics**

Figure 1. Static Characteristic

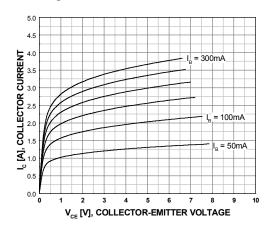


Figure 3. DC Current Gain (O-Grade)

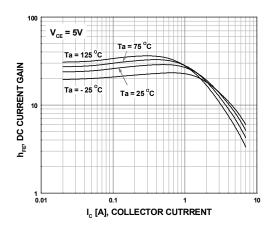


Figure 5. Saturatin Voltage (O-Grade)

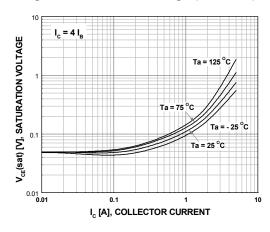


Figure 2. DC Current Gain (R-Grade)

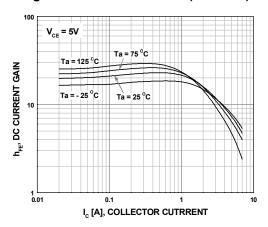


Figure 4. Saturation Voltage (R-Grade)

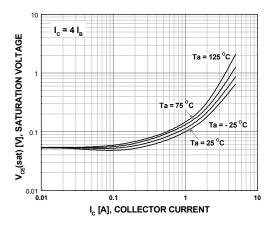
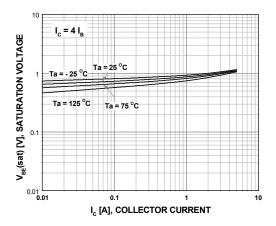


Figure 6. Saturation Voltage (R-Grade)



## **Typical Characteristics**

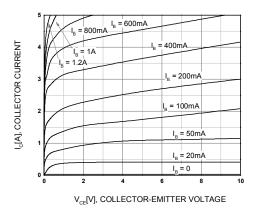


Figure 1. Static Characteristic

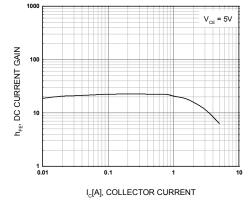


Figure 2. DC current Gain

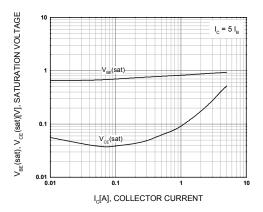


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

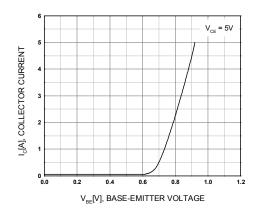


Figure 4. Base-Emitter On Voltage

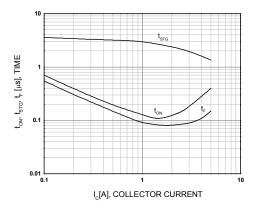


Figure 5. Switching Time

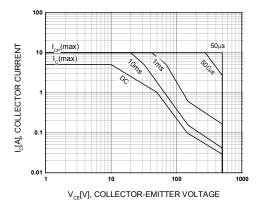


Figure 6. Safe Operating Area

# **Typical Characteristics** (Continued)

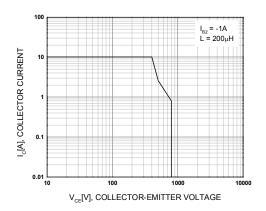


Figure 7. Reverse Bias Safe Operating Area

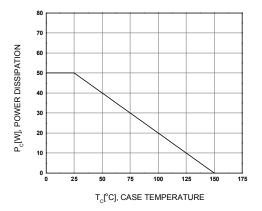
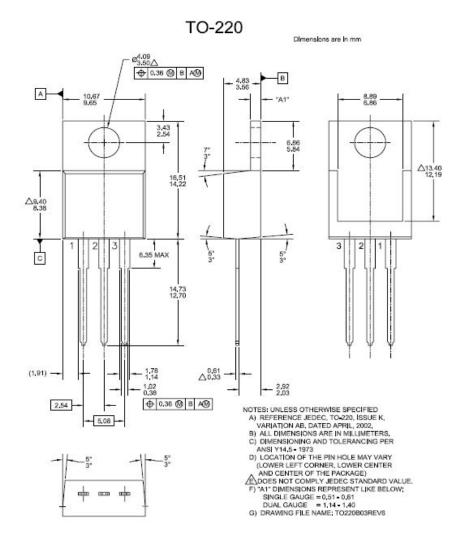


Figure 8. Power Derating

## **Package Dimension**







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